L Number	Hits	Search Text	DB	Time stamp
-	1192	@ad<=20010104 and 'heating substrate' and 'amorphous silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 14:28
-	943	((438/486) or (438/482)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:05
-	71	(((438/486) or (438/482)).CCLS.) and @ad<=20010104 and 'heating substrate' and 'amorphous silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:00
-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and @ad<=20010104 and 'heating substrate' and 'amorphous silicon' and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:18
-	2	(((438/486) or (438/482)).CCLS.) and MILC and 'low temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:36
-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and MILC and 'low temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:06
-	0	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating' with 'while depositing'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:11
-	181	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:11
-	109	(@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating') and 'depositing'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:11
-	14	@ad<=20010104 and 'amorphous silicon' with 'metal layer' and 'heating' with 'depositing'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:11
-	2	(@ad<=20010104 and 'heating substrate' and 'amorphous silicon') and @ad<=20010104 and 'amorphous silicon' and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:10
-	303	(((438/486) or (438/482)).CCLS.) and 'low temperature'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:37
-	52	(((438/486) or (438/482)).CCLS.) and 'low temperature' and 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/03 13:37
-	0	@ad<=20010104 and heating adj1 substrate with depositing same metal and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:51

-	58	@ad<=20010104 and MILC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:18
-	0	@ad<=20010104 and heating adj1 substrate adj1 while same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:54
-	0	@ad<=20010104 and heat adj1 substrate adj1 while same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:54
-	3	@ad<=20010104 and heat adj1 substrate same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 13:56
-	74	@ad<=20010104 and heating adj1 substrate same 'depositing metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 14:15
-	15	@ad<=20010104 and 'hot metallization'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 14:16
-	191	@ad<=20010104 and 'amorphous silicon' same 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 15:55
-	12	@ad<=20010104 and 'amorphous silicon' same 'heating substrate' same 'metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 15:40
-	3778	((438/149) or (438/158) or (438/315) or (438/334) or (257/57)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 15:42
-	54	(((438/149) or (438/158) or (438/315) or (438/334) or (257/57)).CCLS.) and @ad<=20010104 and 'heating substrate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/24 15:56